



A15 Superconductors by

Thermal Diffusion in 6 GHz Cavities

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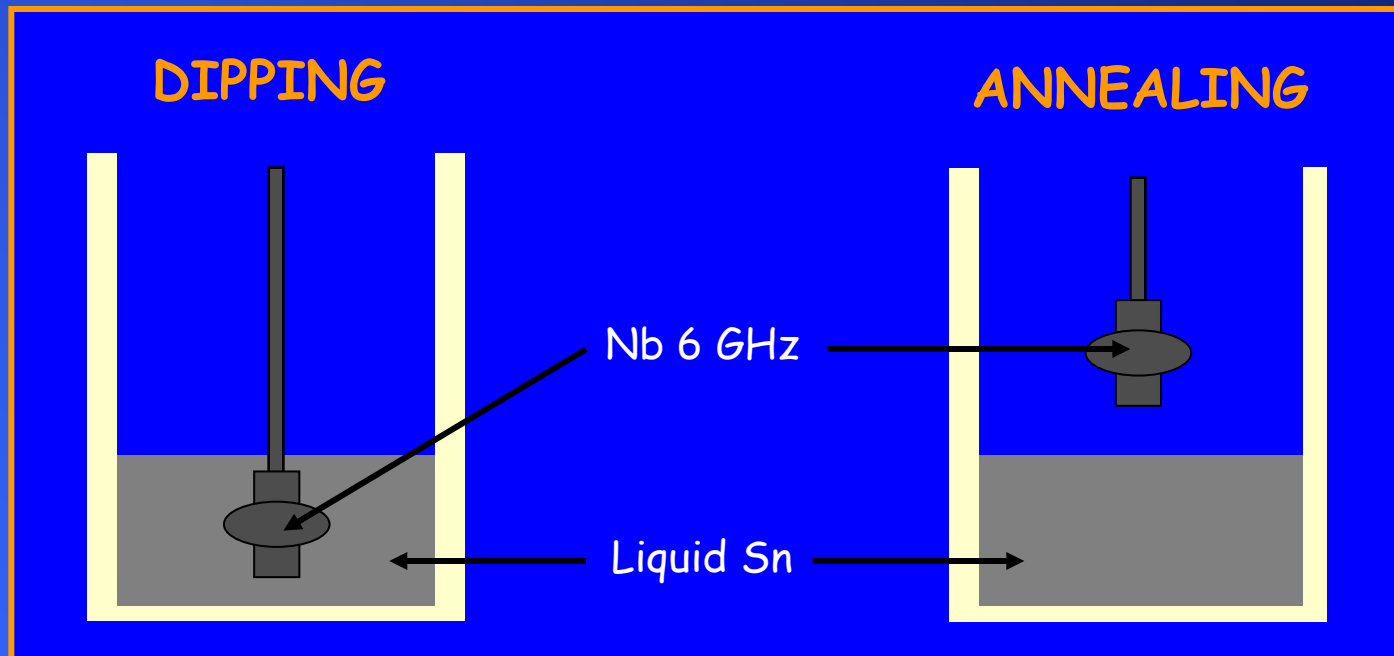
° IUAC, New Delhi, India



TECHNIQUE

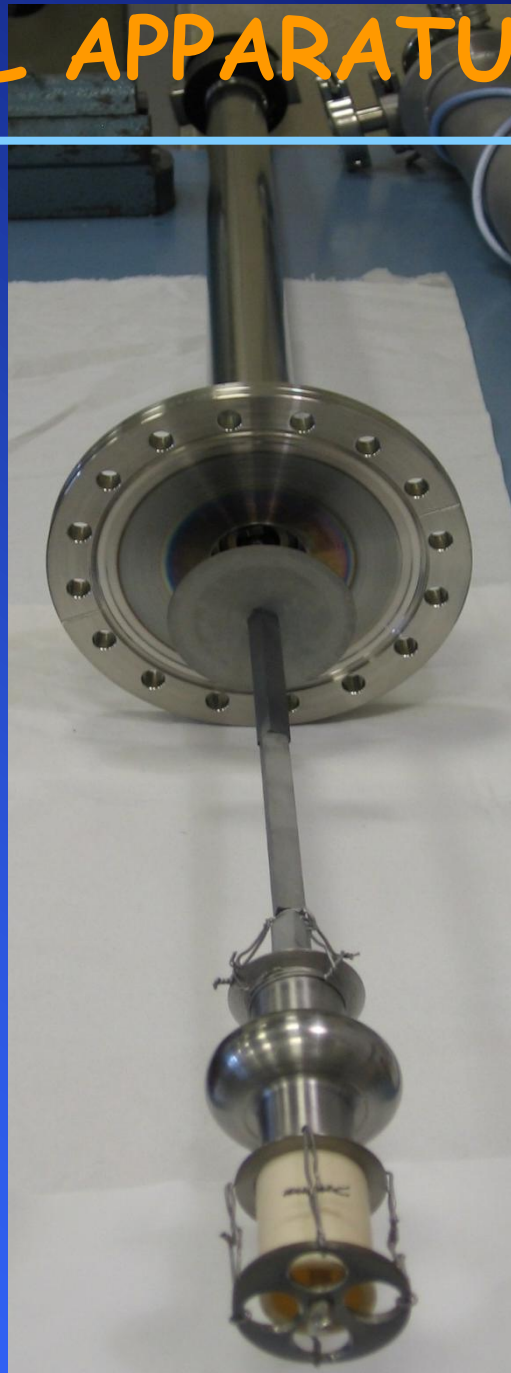
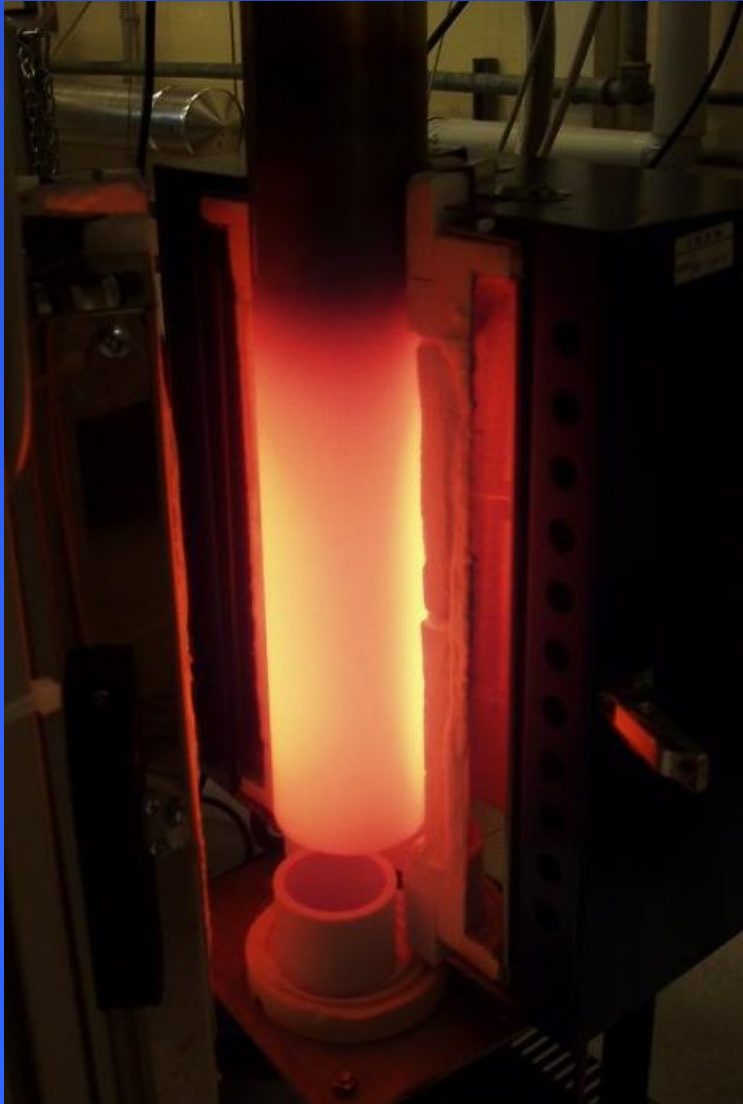
Nb_3Sn is obtained through

THE LIQUID Sn DIFFUSION TECHNIQUE



- No nucleation sites on Nb are required
- Fast growth of Nb_3Sn layer

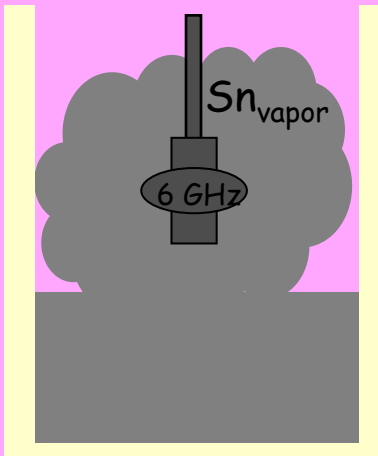
EXPERIMENTAL APPARATUS



THREE PROCEDURES

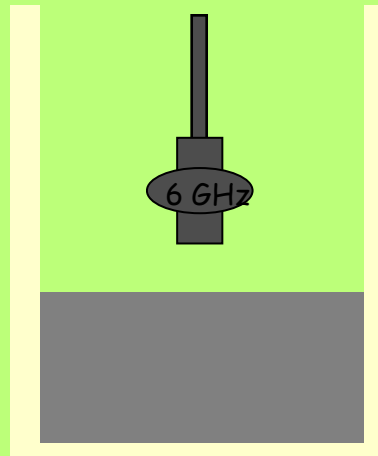
1

**Sn vapor
Annealing**



2

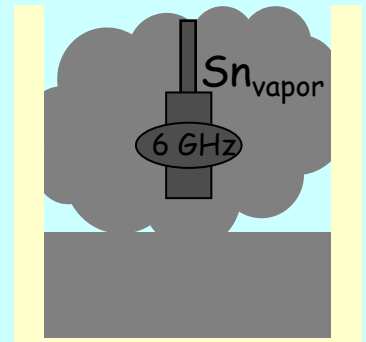
**Vacuum
Annealing**



3

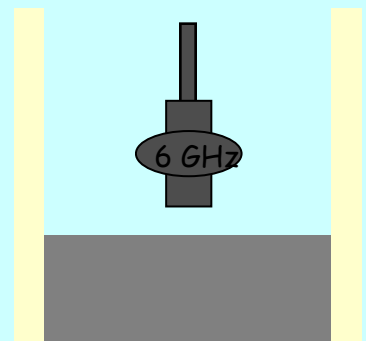
**Double
Process**

**Sn vapor
Annealing**



+

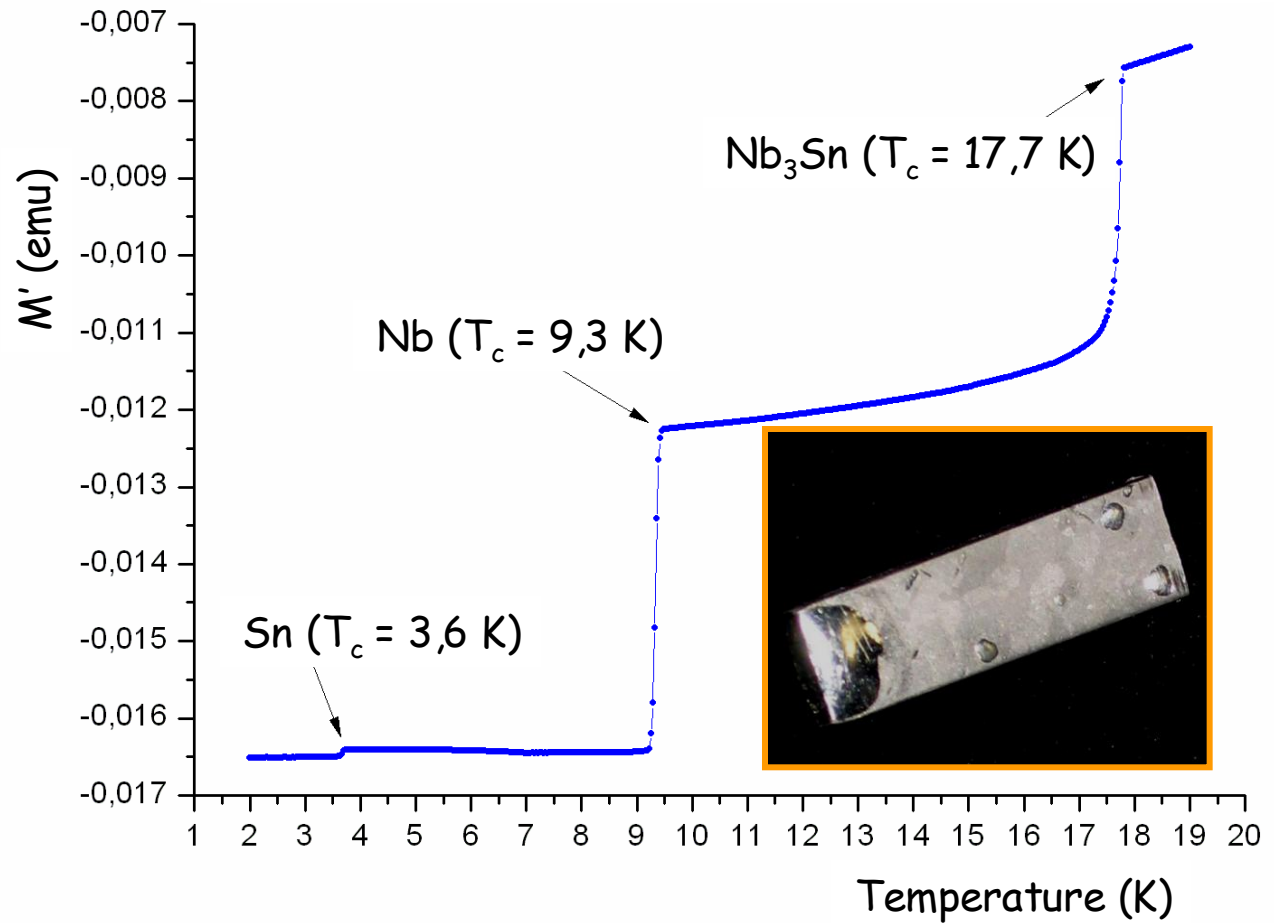
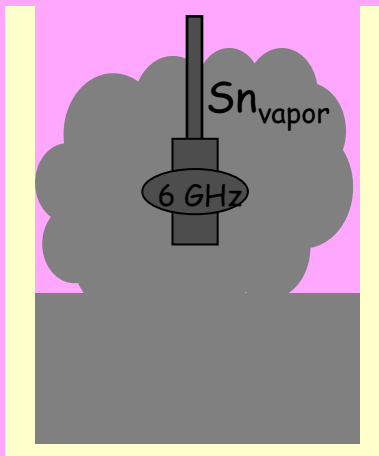
**Vacuum
Annealing**



Sn VAPOR ANNEALING

1

Sn vapor
Annealing

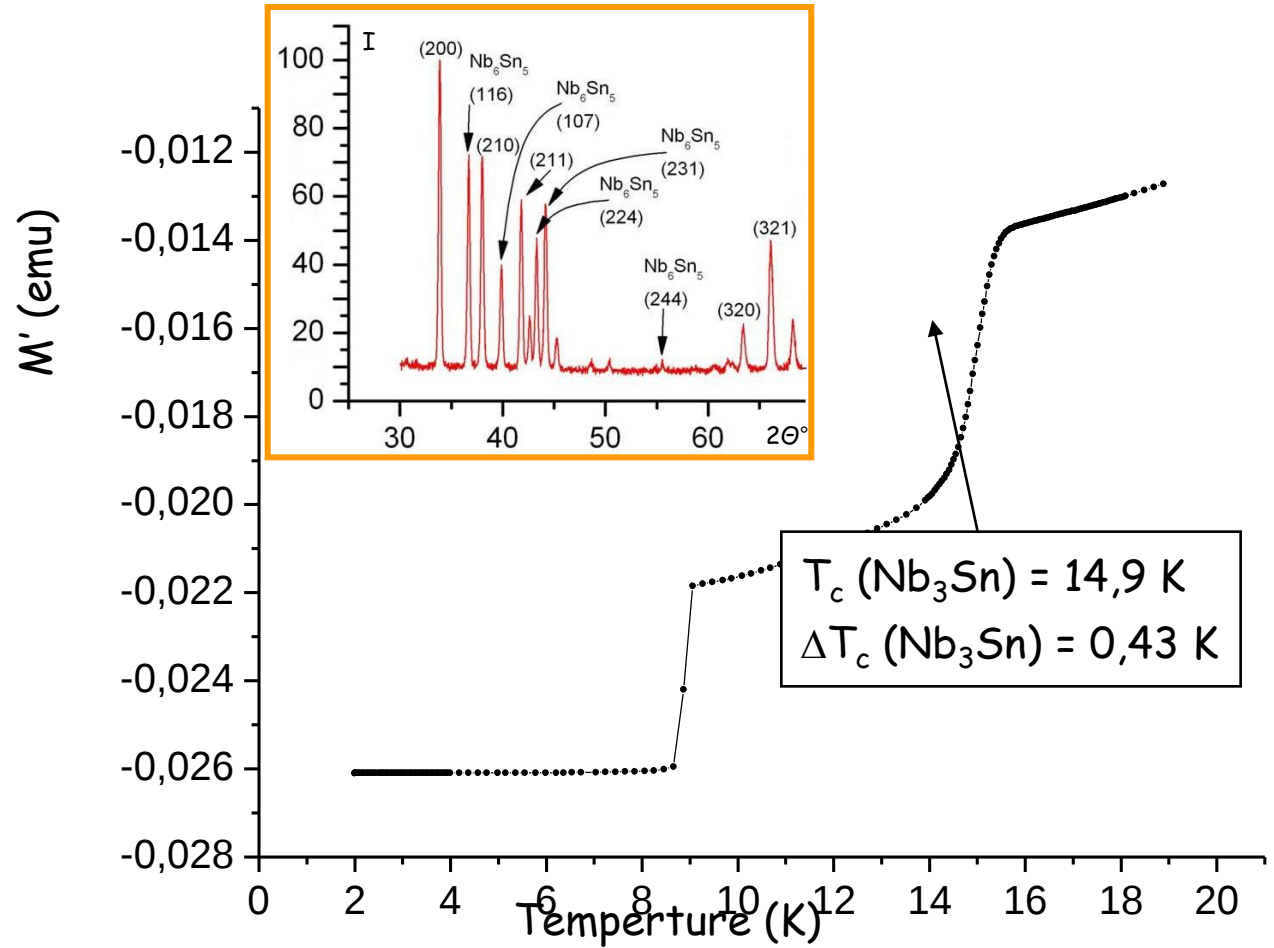
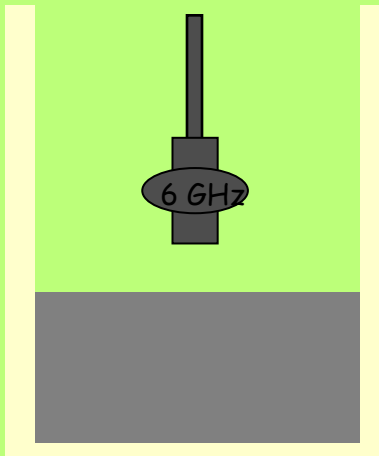


- residual Sn
- spurious phases

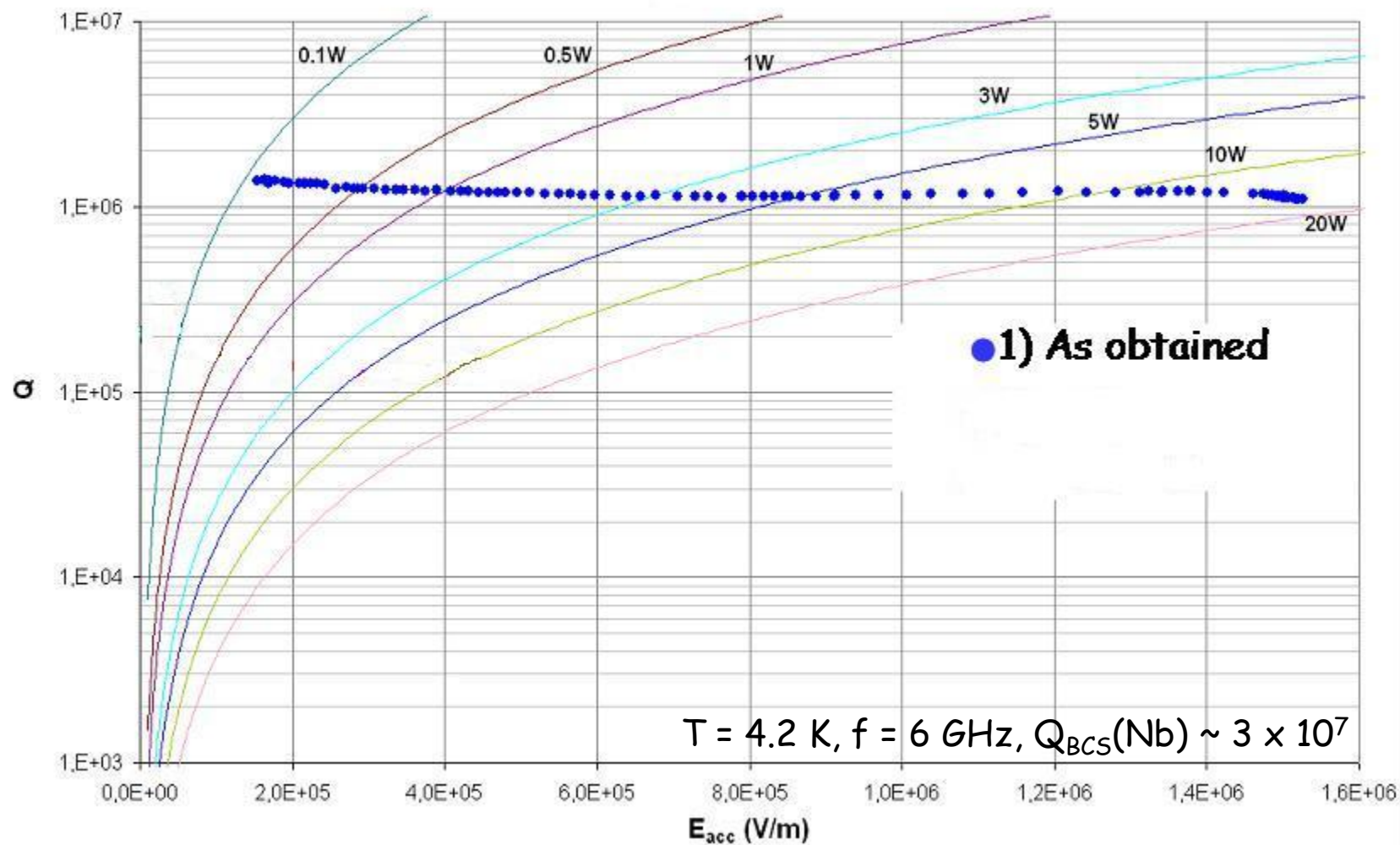
VACUUM ANNEALING

2

Vacuum
Annealing



- low T_c s
- spurious phases

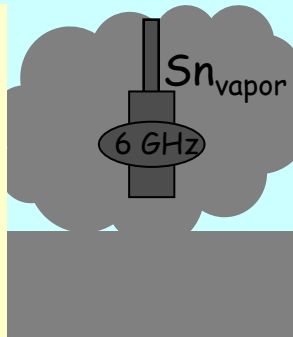


DOUBLE PROCESS

3

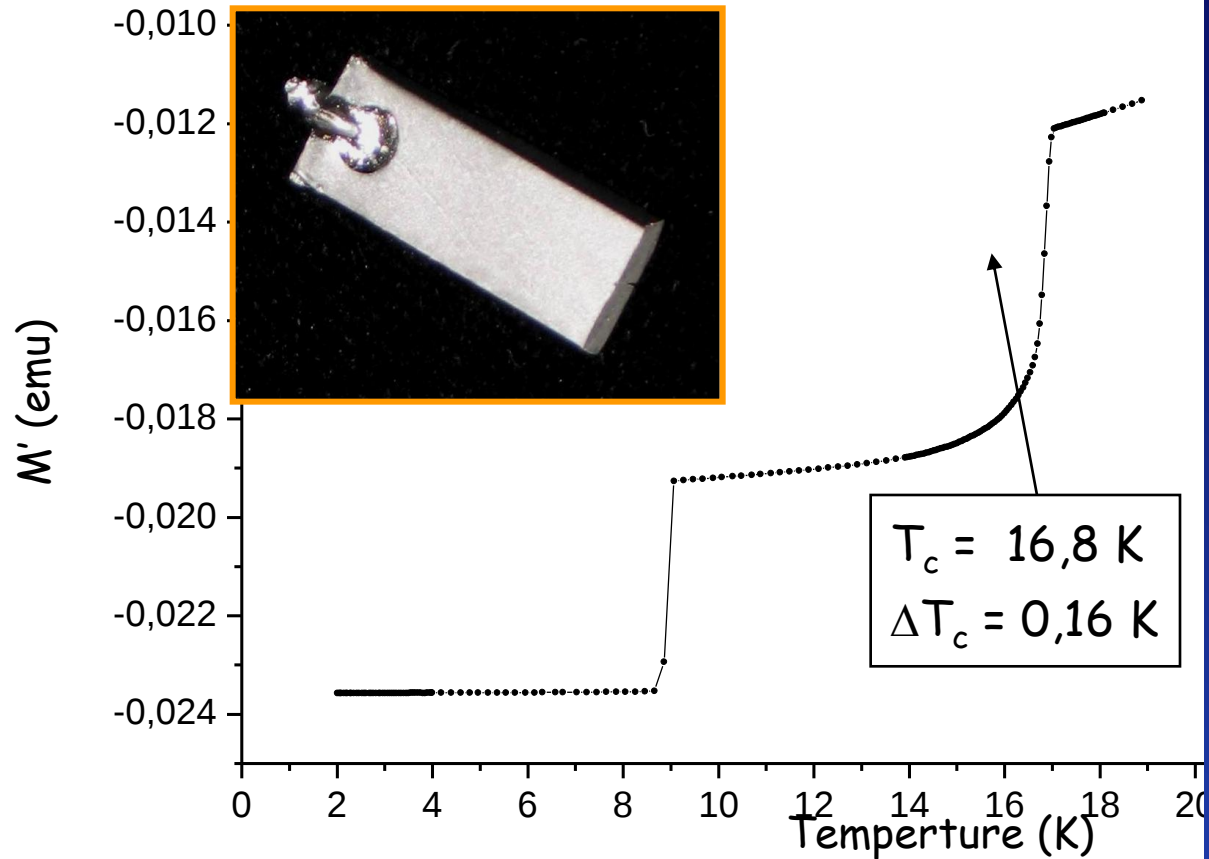
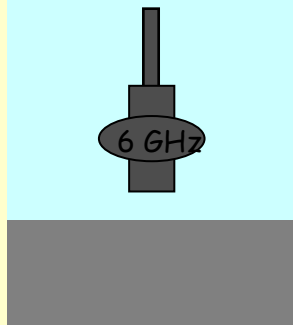
Double
Process

Sn vapor
Annealing



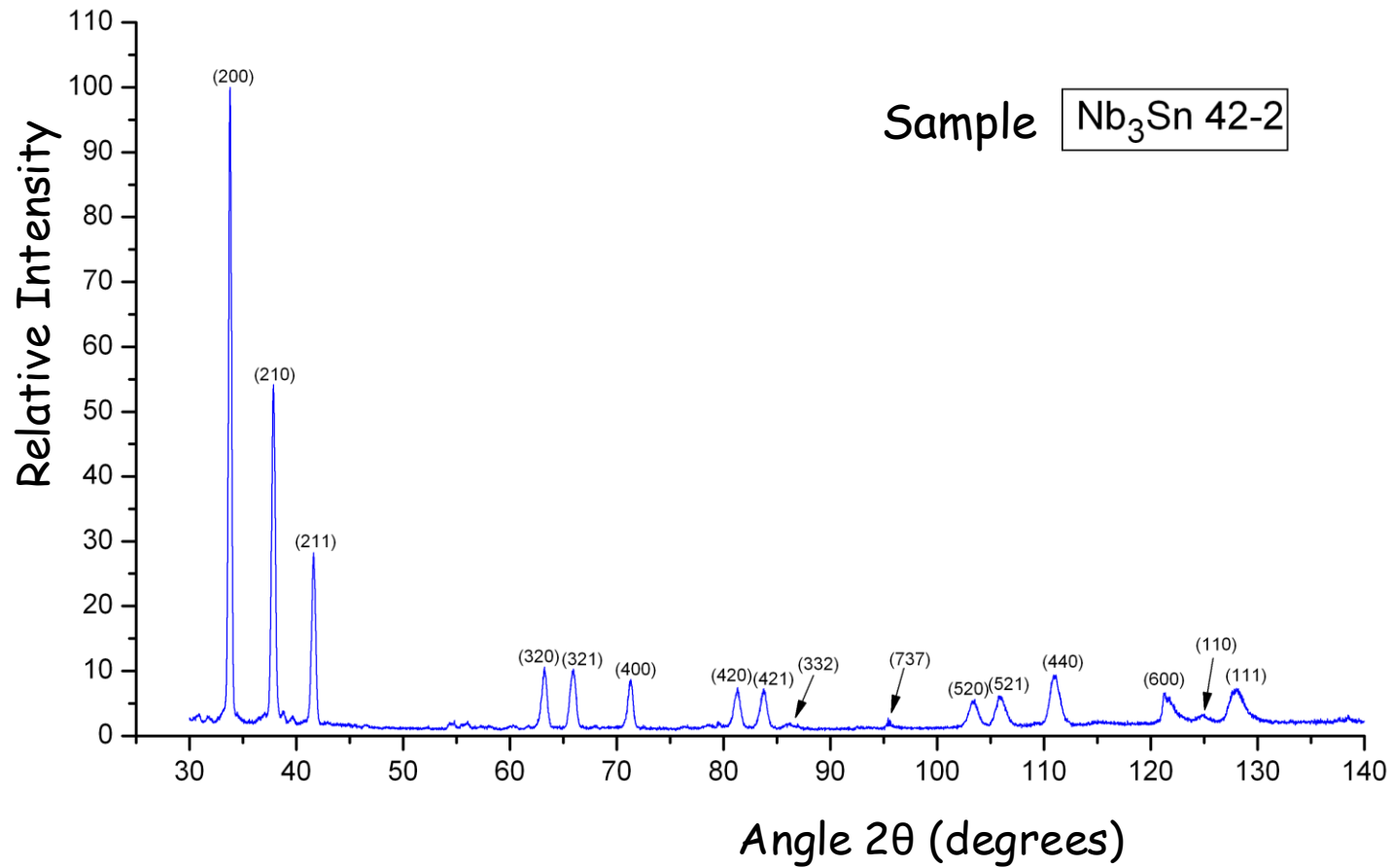
+

Vacuum
Annealing



- good T_c s,
- no residual Sn,
- no spurious phases

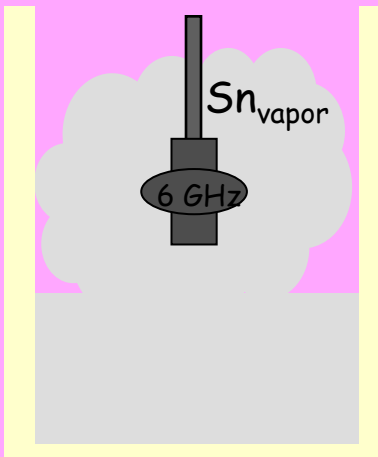
XRD



THE CHOSEN PROCEDURE

1

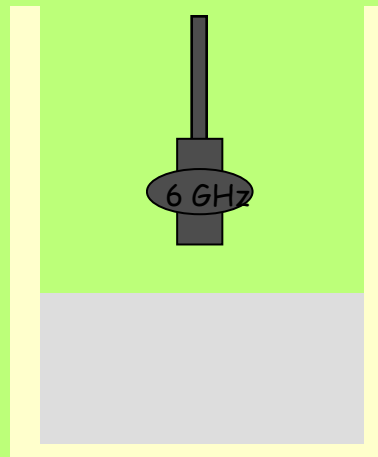
Sn vapor
Annealing



- residual Sn
- spurious phases

2

Vacuum
Annealing

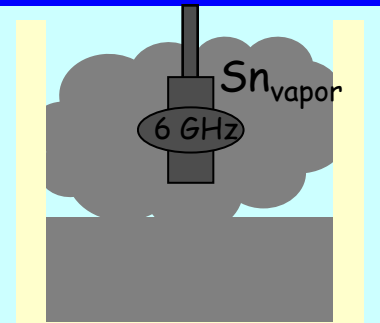


- low T_c s
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3

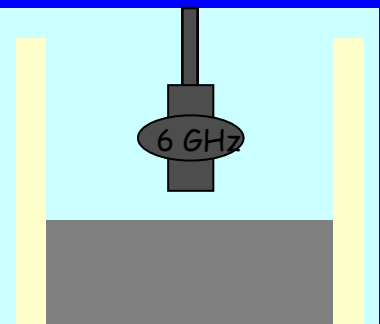
Double
Process

Sn vapor
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+

Vacuum
Annealing



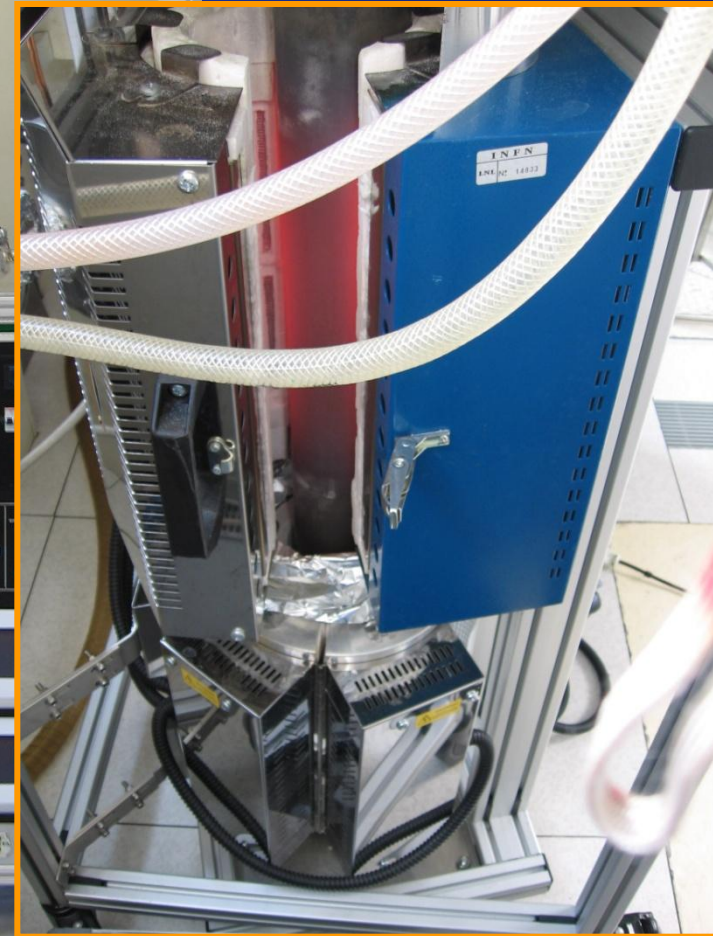
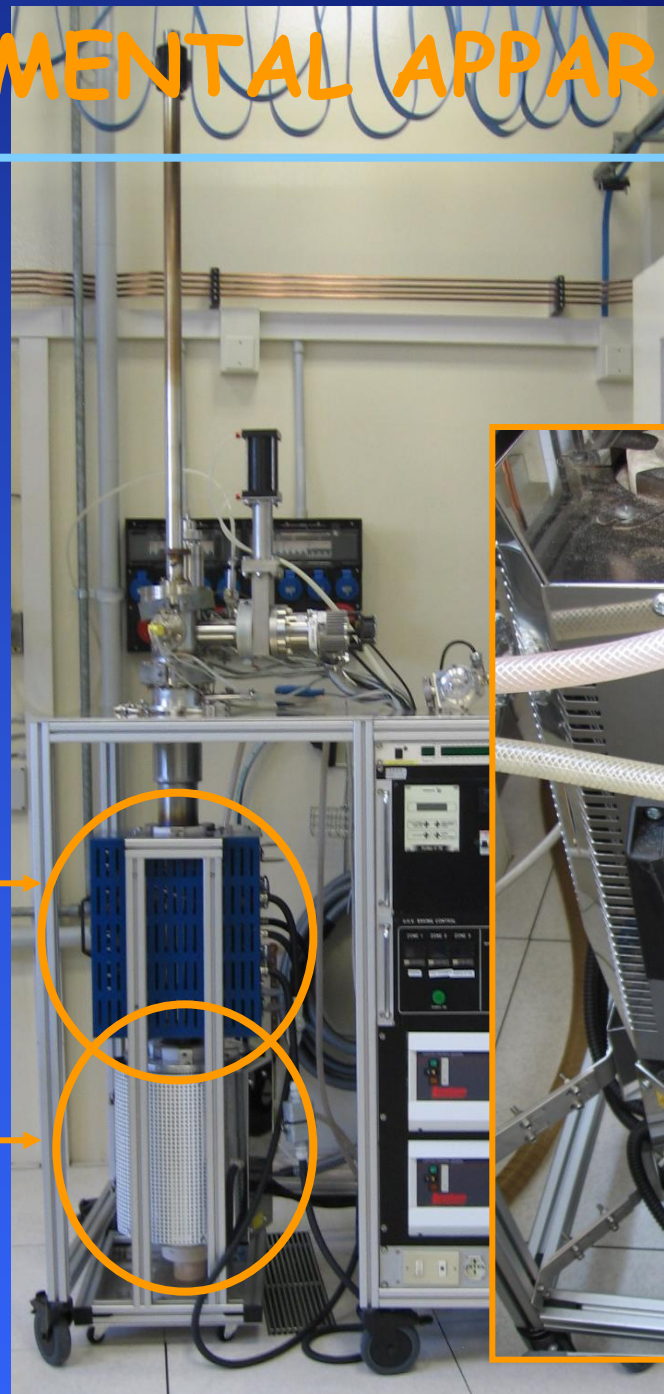
- good T_c s,
- no residual Sn,
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NEW EXPERIMENTAL APPARATUS

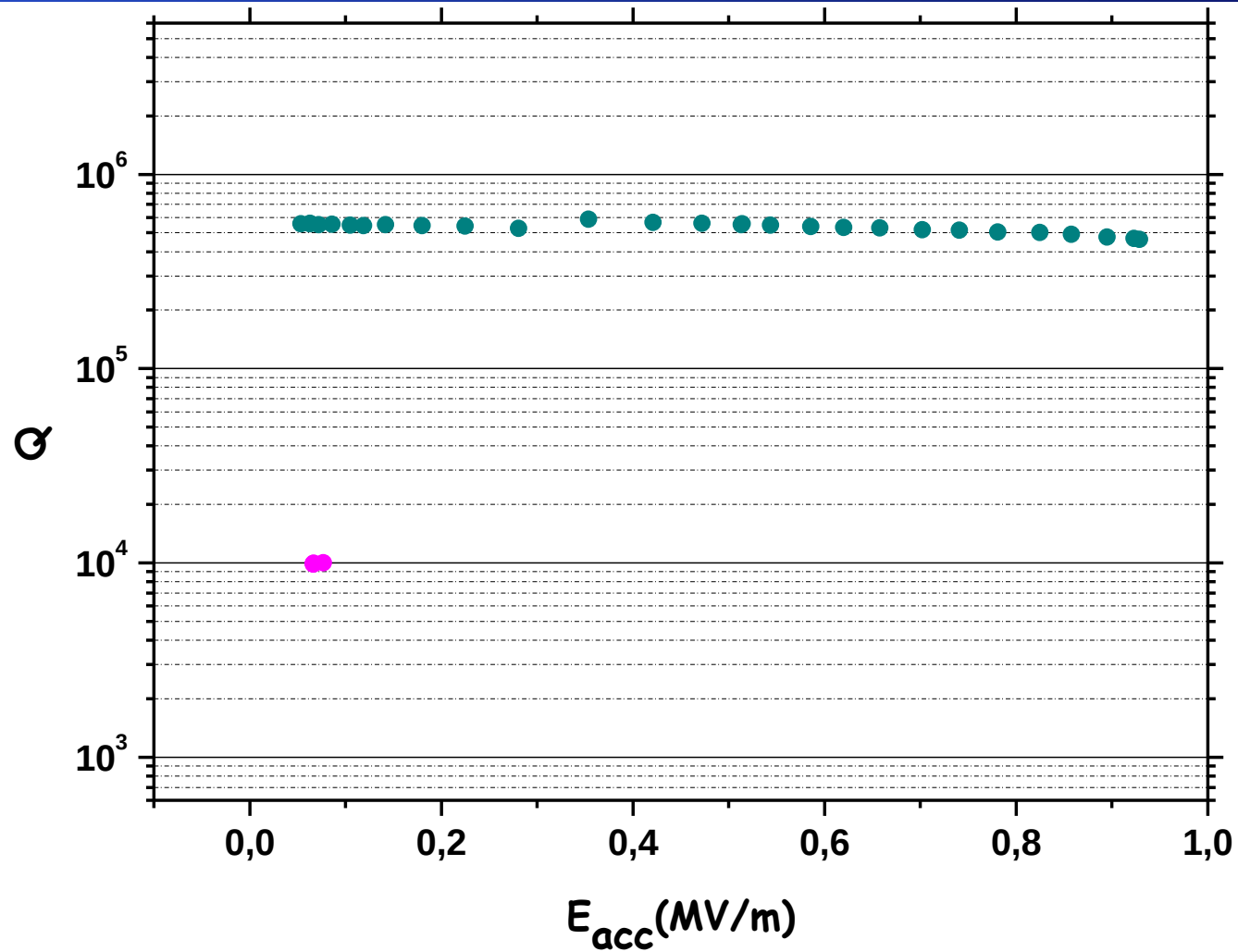
No air contamination while opening the vacuum system

Annealing Furnace

Dipping Furnace

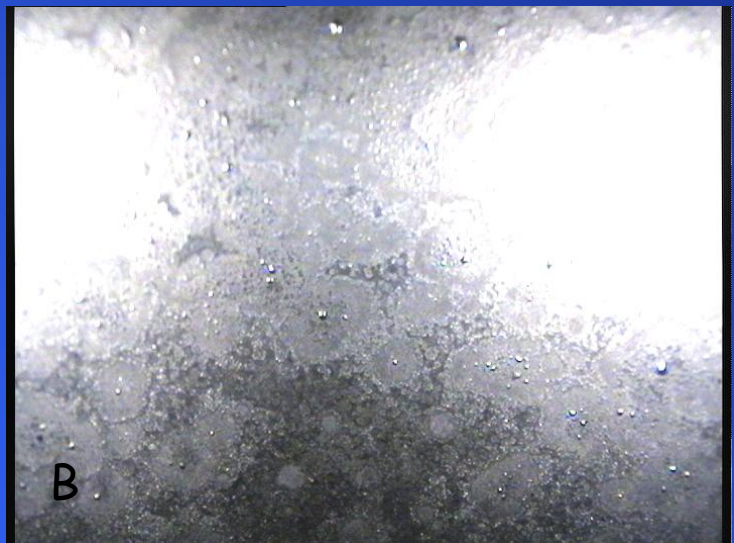
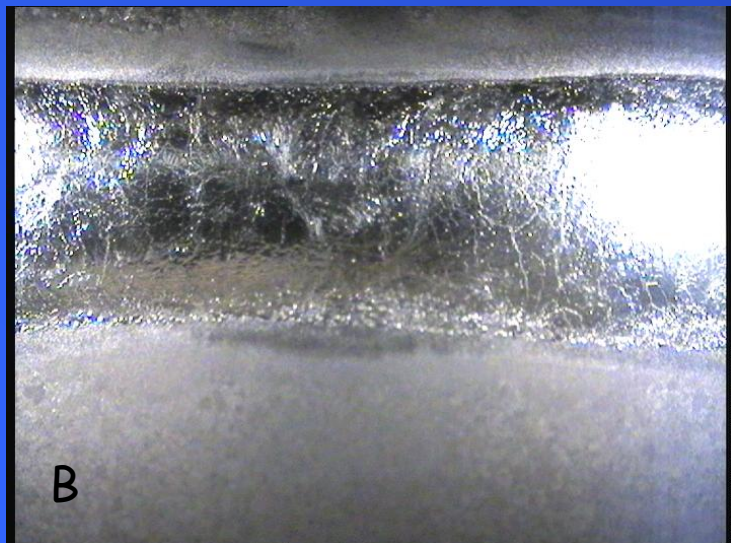
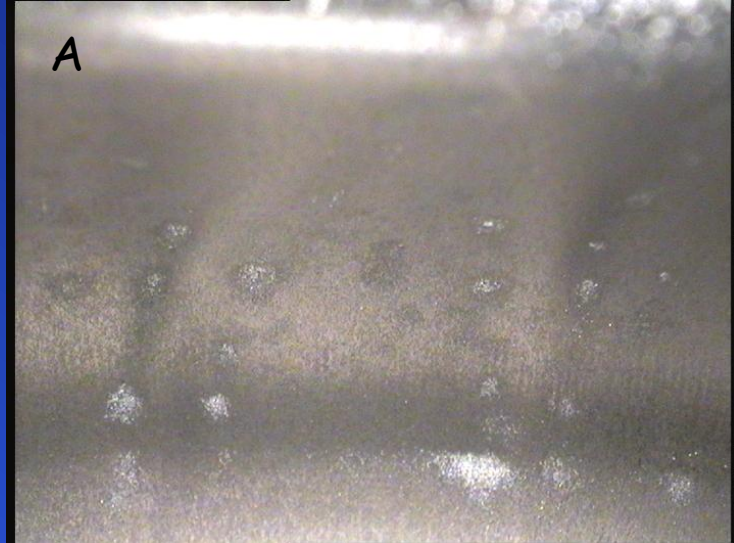


Q vs E_{acc}



$T = 4.2$ K, $f = 6$ GHz, $Q_{BCS}(\text{Nb}) \sim 3 \times 10^7$

OPTICAL DIAGNOSTIC

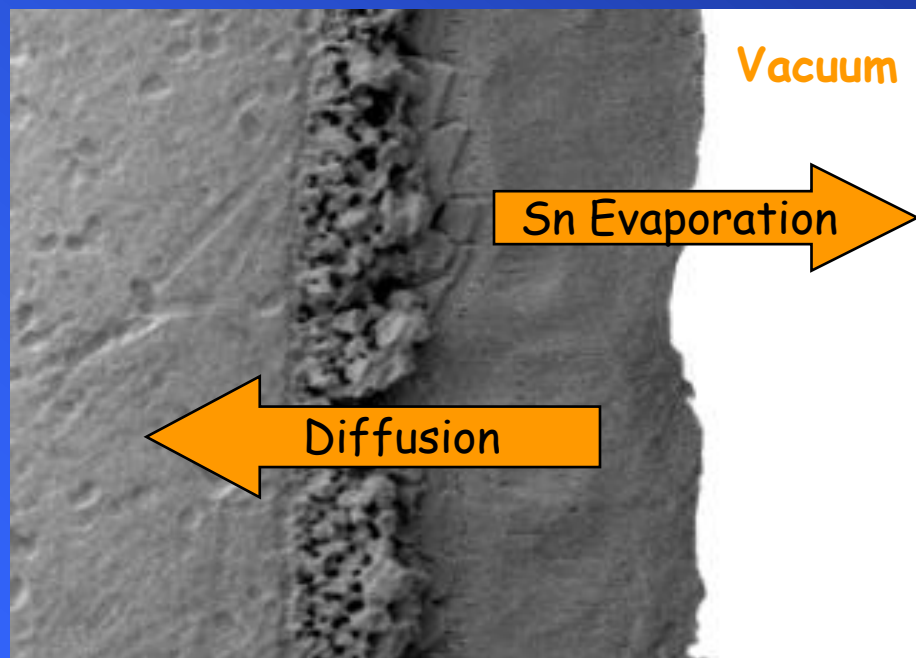
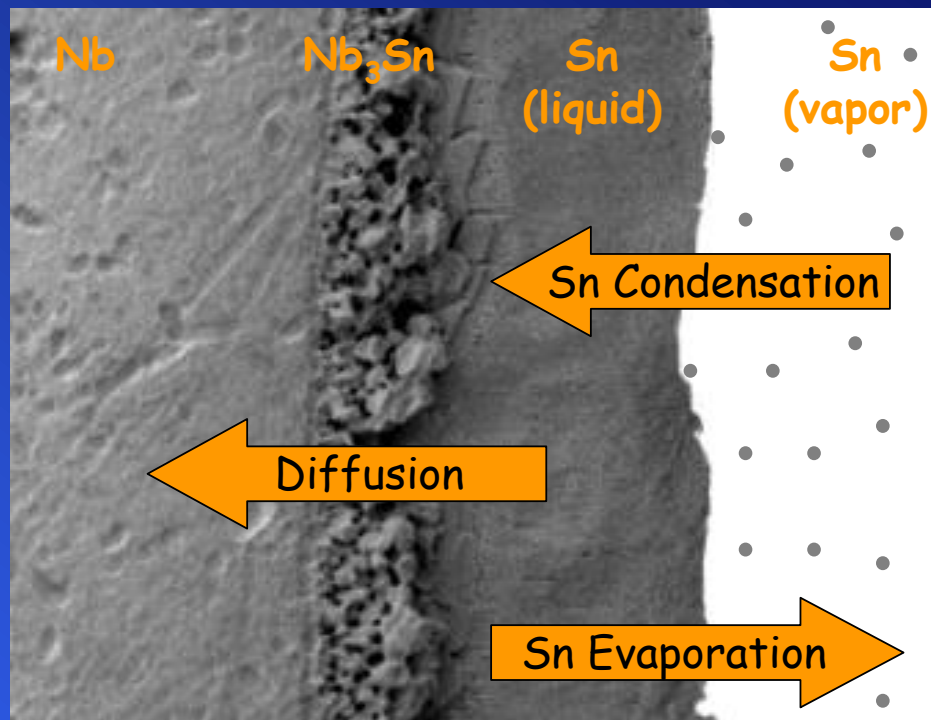


PRESENT WORK

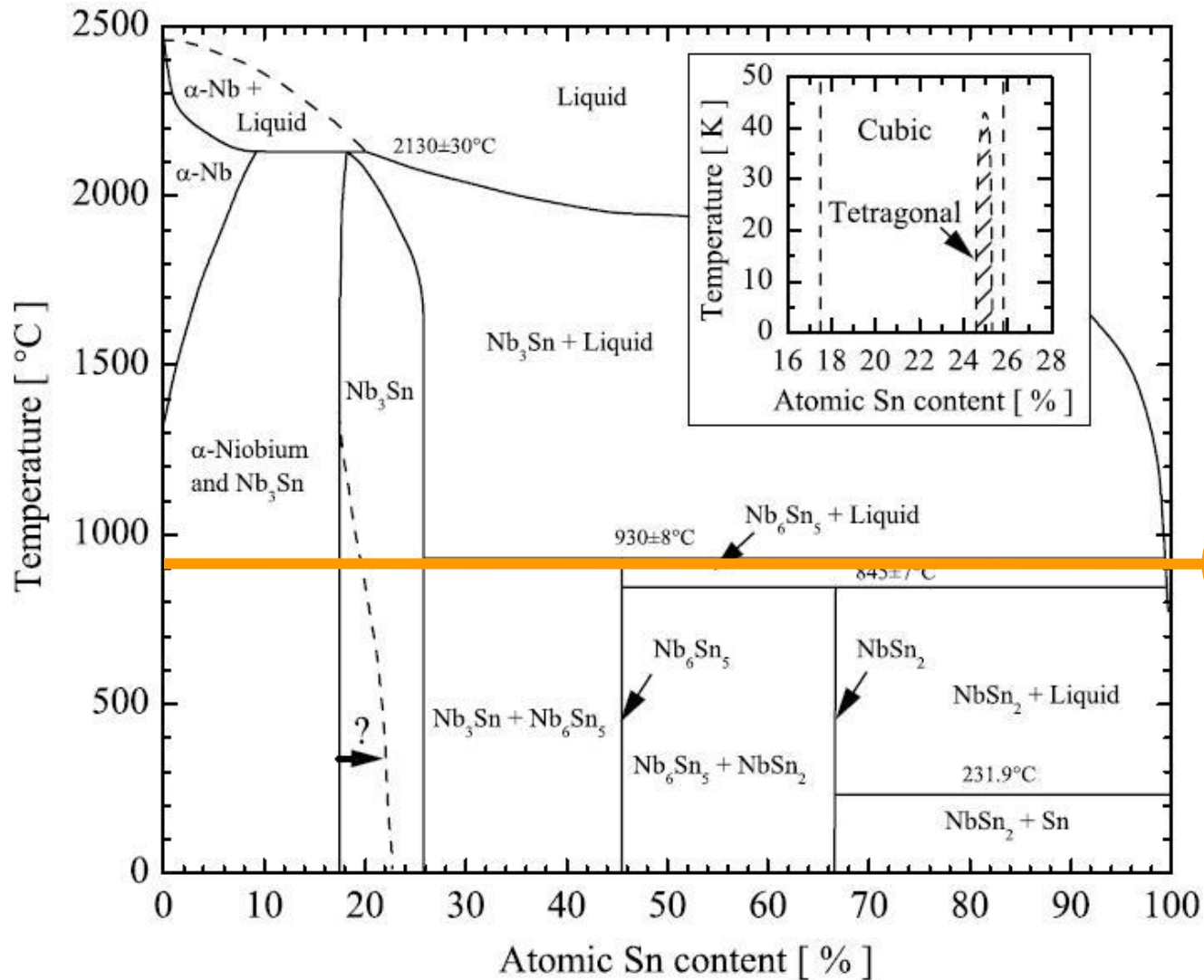
1) Droplets elimination changing the process T and t

2) Chemical polishing

3) Prevent Sn droplets through the cavity vibration



WORKING TEMPERATURE



930°C

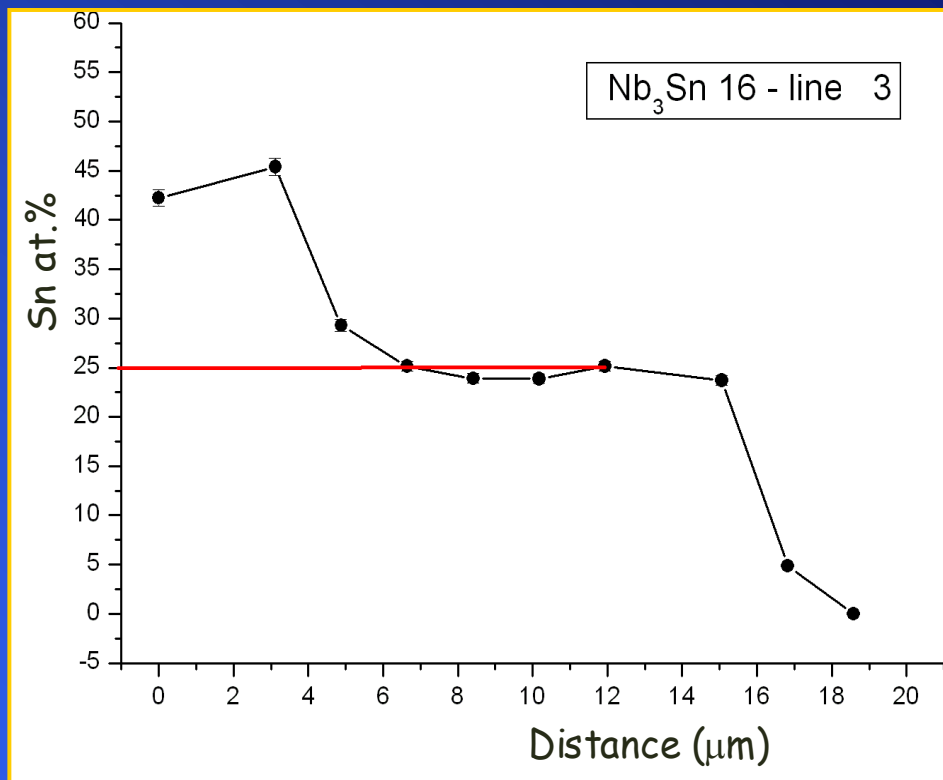
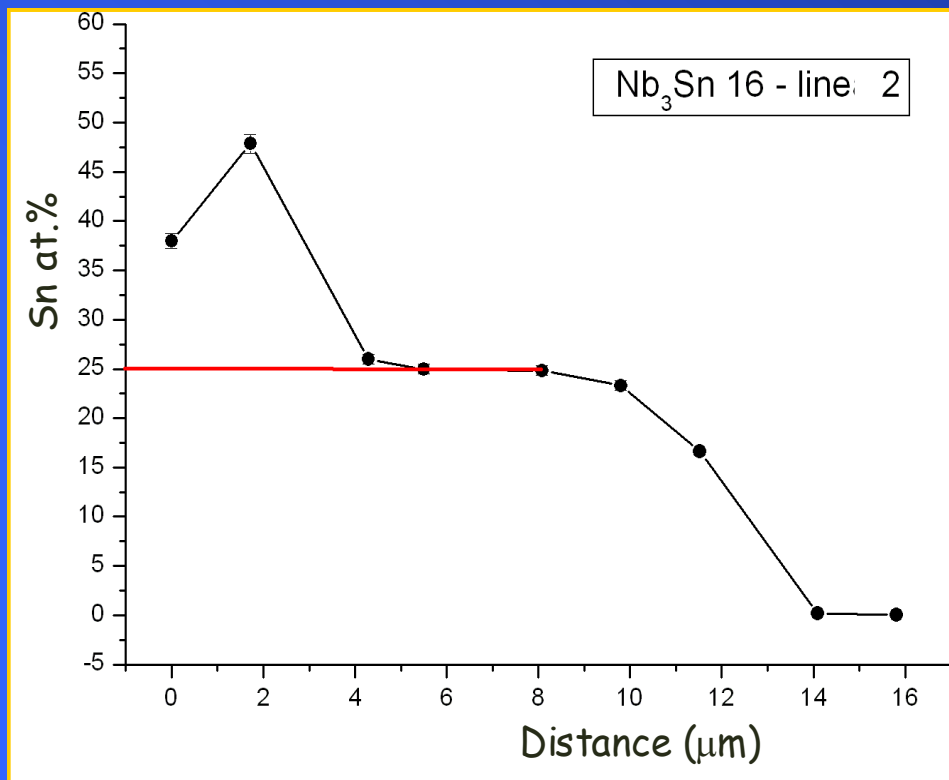
PRESENT WORK

1) Droplets elimination changing the process T and t

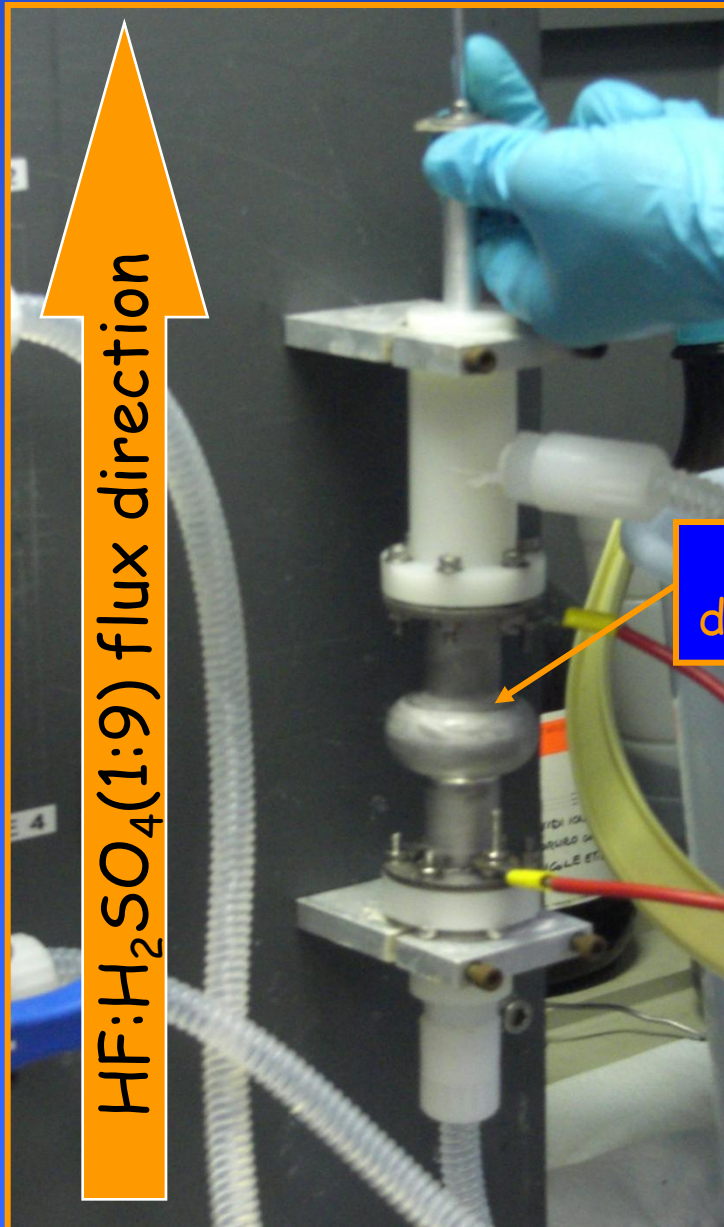
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ELECTRON MICROPROBE ANALYSIS



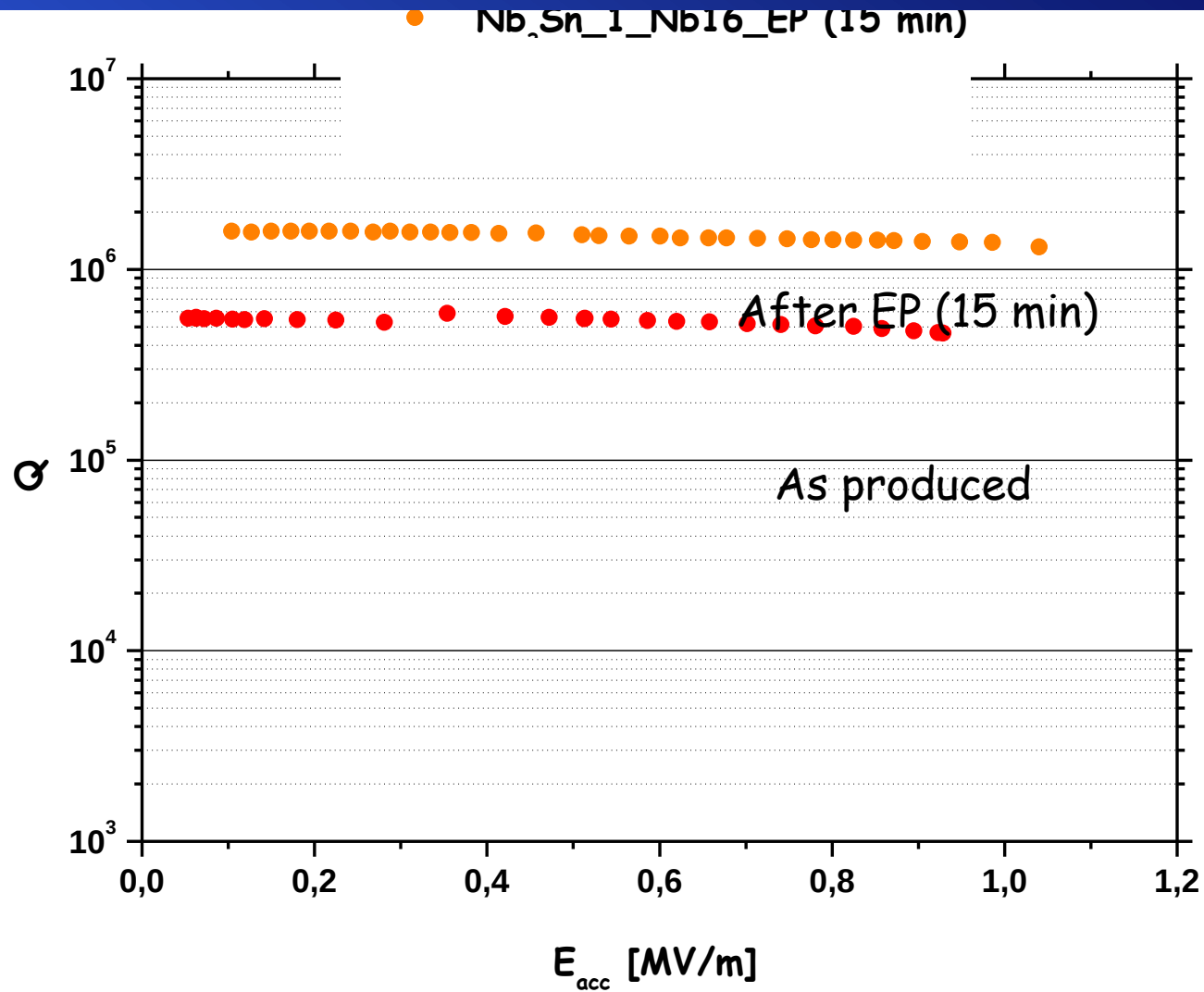
Nb₃Sn CHEMICAL POLISHING



It can be possible to:

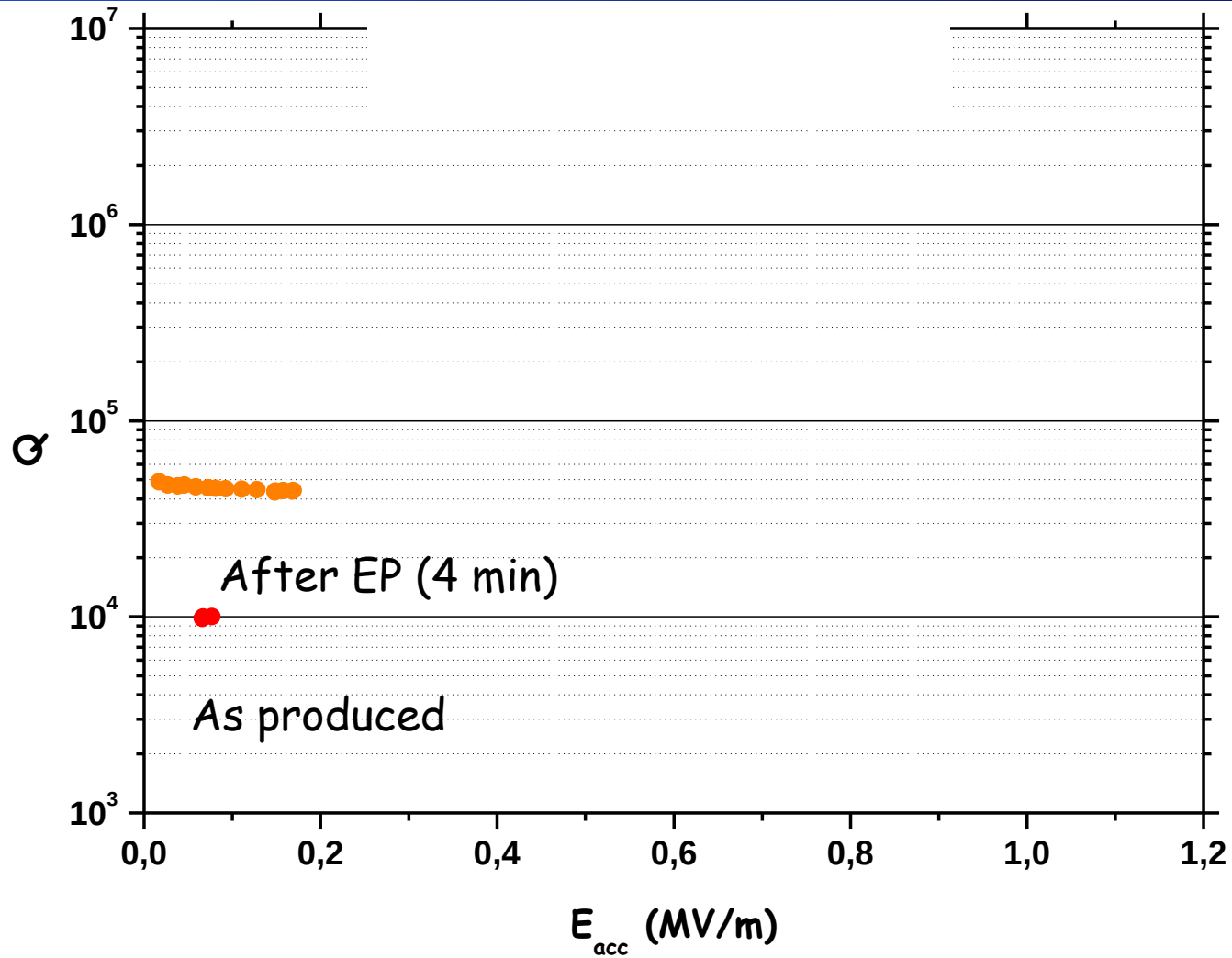
- Get rid of unreacted Sn
- Remove the first Nb₃Sn layer (stoichiometry?)

Q vs E_{acc}



$T = 4.2 \text{ K}$, $Q_{BCS}(\text{Nb}) \sim 3 \times 10^7$

Q vs E_{acc}



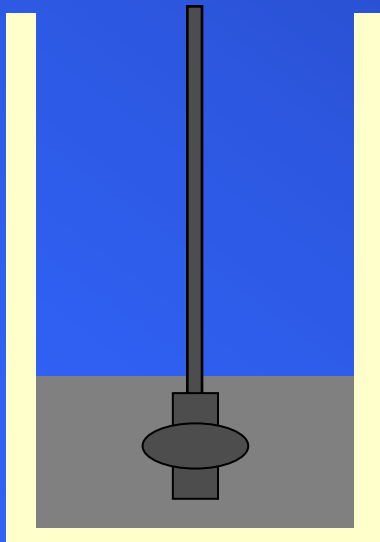
$T = 4.2$ K, $Q_{BCS}(Nb) \sim 3 \times 10^7$

PRESENT WORK

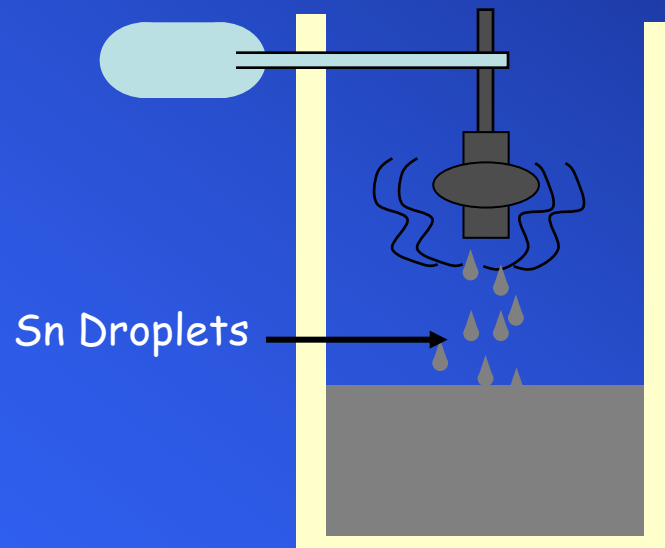
- 1) Droplets elimination changing the process T and t
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CAVITY VIBRATION

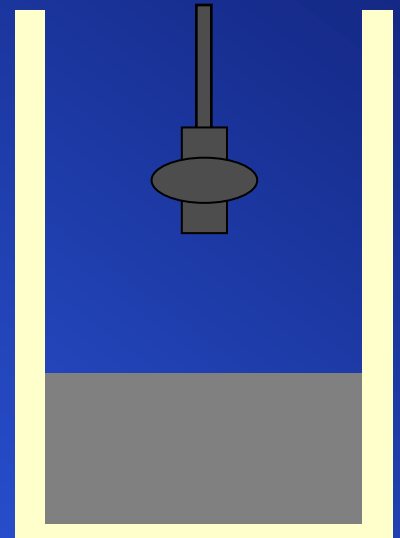
DIPPING



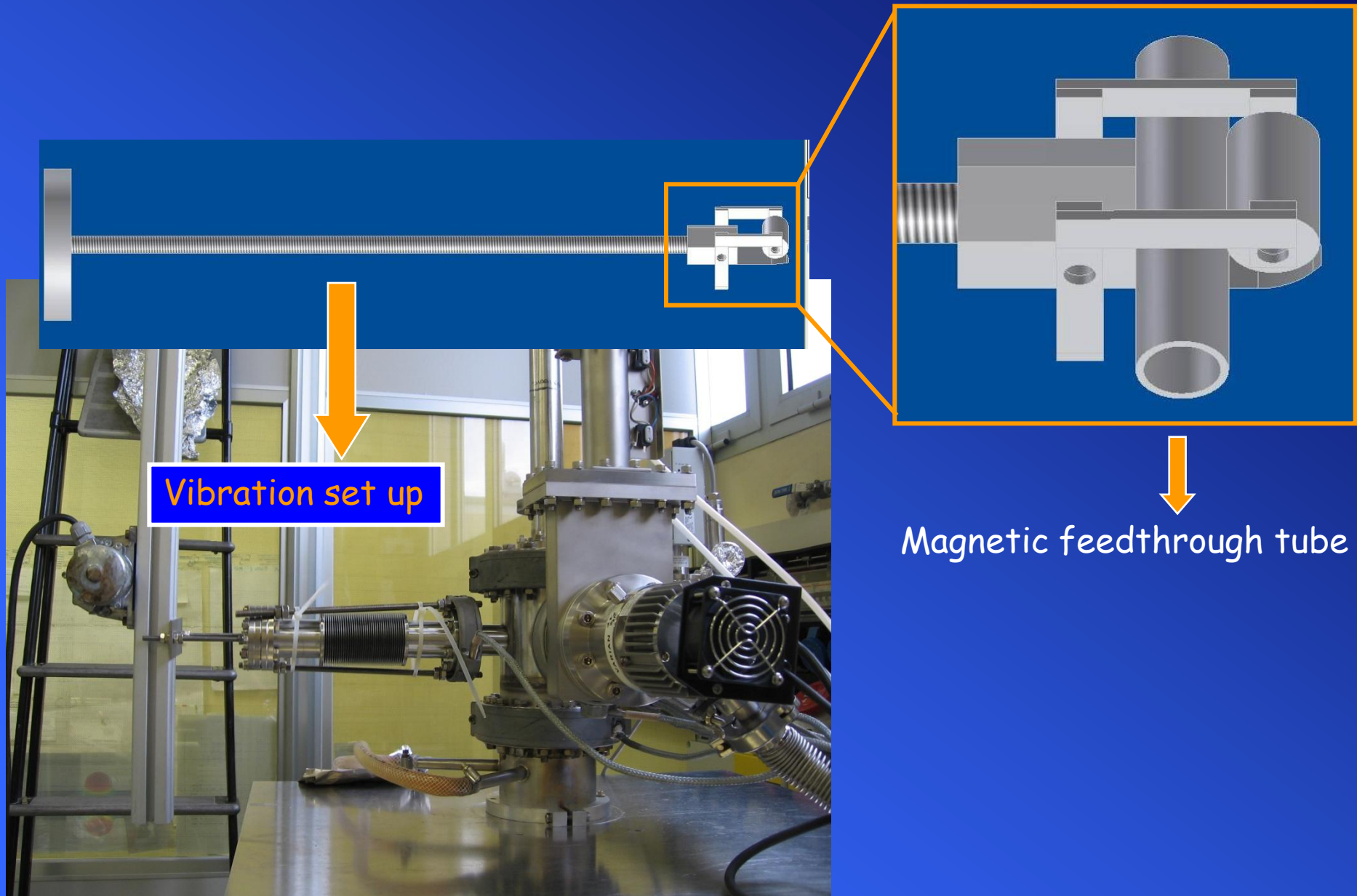
VIBRATION



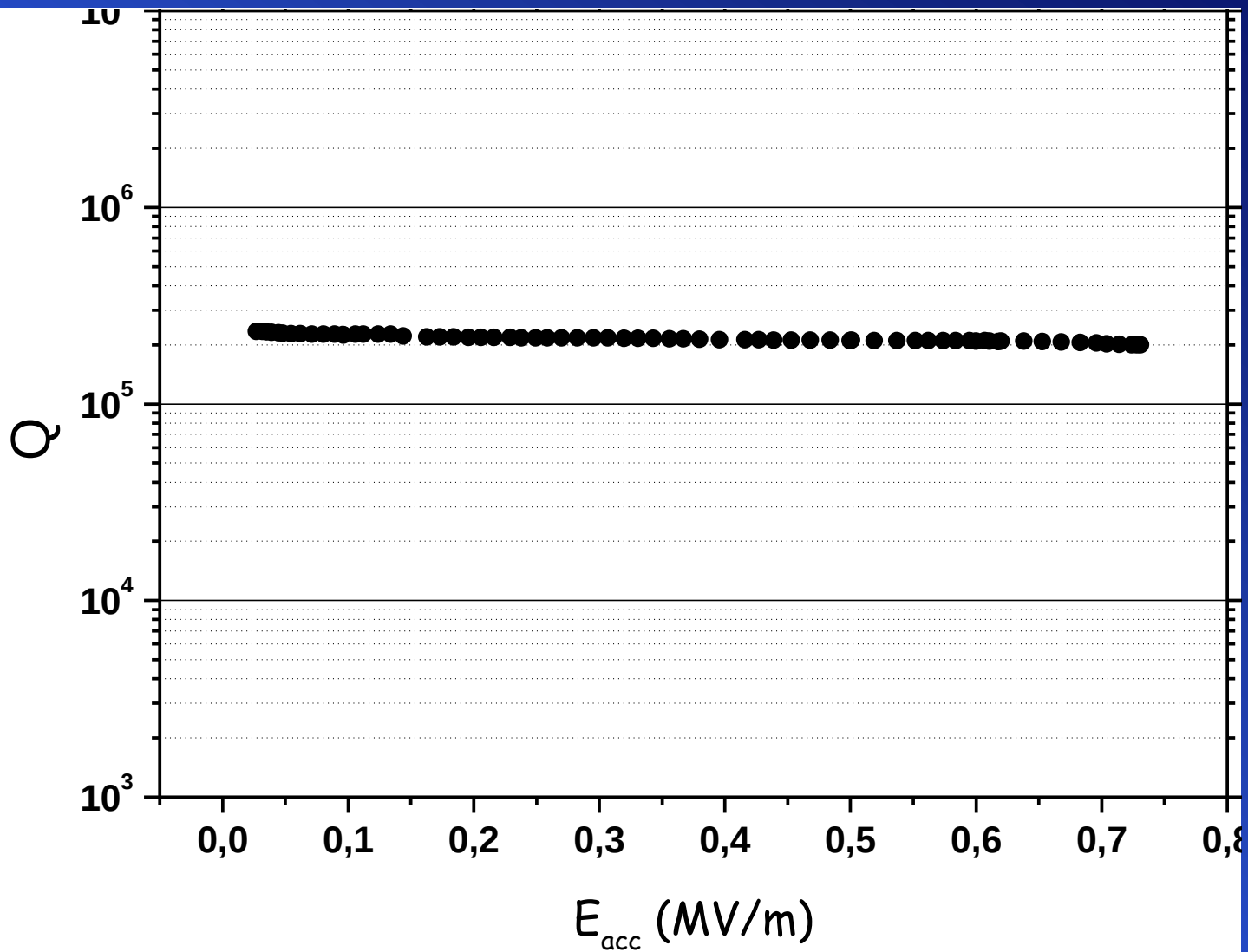
ANNEALING



EXPERIMENTAL APPARATUS



Q vs E_{acc}



$T = 4.2 \text{ K}$, $Q_{BCS}(\text{Nb}) \sim 3 \times 10^7$

DISCUSSION

- We have a promising way to produce Nb_3Sn
- We have 6 GHz cavities that are easy to produce and test
- We have ideas to try to avoid spurious problems

I would like to profit of this opportunity to

DISCUSSION

- We have a promising way to produce Nb_3Sn
- We have 6 GHz cavities that are easy to produce and test
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I would like to profit of this opportunity to

ask you **suggestions!**

How can we modify the process to improve our results?

Thank you!